



TB0640H - TB3500H

100A BIDIRECTIONAL SURFACE MOUNT THYRISTOR SURGE PROTECTIVE DEVICE

Features

- 100A Peak Pulse Current @ 10/1000μs
- 400A Peak Pulse Current @ 8/20μs
- 58 320V Stand-Off Voltages
- Oxide-Glass Passivated Junction
- Bidirectional Protection In a Single Device
- High Off-State Impedance and Low On-State Voltage
- Helps Equipment Meet GR-1089-CORE, IEC 61000-4-5, FCC Part 68, ITU-T K.20/K.21, and UL497B
- UL Listed Under Recognized Component Index, File Number 156346
- Lead Free Finish/RoHS Compliant (Note 1)
- Green Molding Compound (No Halogen and Antimony)
 (Note 2)

Mechanical Data

- Case: SMB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Lead Free Plating (Matte Tin Finish). Solderable per MIL-STD-202, Method 208
- Polarity: None; Bidirectional Devices Have No Polarity Indicator
- Weight: 0.093 grams (approximate)



Top View



Bottom View

Ordering Information (Note 3)

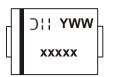
Part Number	Case	Packaging
TB0640H-13-F	SMB	3000/Tape & Reel
TB0720H-13-F	SMB	3000/Tape & Reel
TB0900H-13-F	SMB	3000/Tape & Reel
TB1100H-13-F	SMB	3000/Tape & Reel
TB1300H-13-F	SMB	3000/Tape & Reel
TB1500H-13-F	SMB	3000/Tape & Reel
TB1800H-13-F	SMB	3000/Tape & Reel
TB2300H-13-F	SMB	3000/Tape & Reel
TB2600H-13-F	SMB	3000/Tape & Reel
TB3100H-13-F	SMB	3000/Tape & Reel
TB3500H-13-F	SMB	3000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied, see EU Directive 2002/95/EC Annex Notes.

2. Product manufactured with Data Code 0924 (week 24, 2009) and newer are built with Green Molding Compound.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Maximum Ratings @T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

Characteristic		Symbol	Value	Unit
Non-Repetitive Peak Impulse Current	@10/1000us	I _{pp}	100	A
Non-Repetitive Peak On-State Current	@8.3ms (one-half cycle)	I _{TSM}	50	А
Typical Positive Temperature Coefficient for Breakdown Voltage		$\Delta VBR/\Delta T_J$	0.1	%/°C

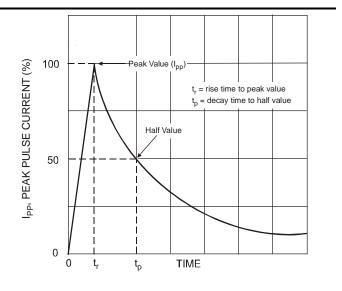
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Lead	R _{θJL}	20	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	100	°C/W
Junction Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	О°

Maximum Rated Surge Waveform

Waveform	Standard	lpp (A)	
2/10µs	GR-1089-CORE	500	
8/20μs	IEC 61000-4-5	400	
10/160µs	FCC Part 68	250	
10/700µs (Note 4)	ITU-T, K.20/K.21	200	
10/560µs	FCC Part 68	160	
10/1000µs	GR-1089-CORE	100	

Notes: 4. Applied 6kV, 10/700µs waveform





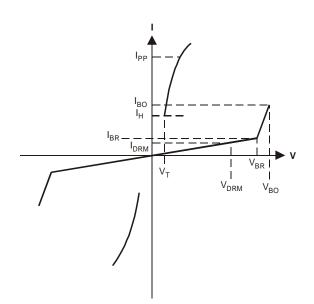
Electrical Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

Part Number	Maximum Rated Repetitive Off-State Voltage	Maximum Off-State Leakage Current @ V _{DRM}	Maximum Breakover Voltage	Maximum On-State Voltage @ I _T = 1A	Cur	kover rent 30		Current	Typical Off-State Capacitance	Marking Code
	V _{DRM} (V)	I _{DRM} (uA)	V _{BO} (V)	V _T (V)	Min (mA)	Max (mA)	Min (mA)	Max (mA)	C _O (pF)	
TB0640H	58	5	77	3.5	50	800	150	800	200	T064H
TB0720H	65	5	88	3.5	50	800	150	800	200	T072H
TB0900H	75	5	98	3.5	50	800	150	800	200	T090H
TB1100H	90	5	130	3.5	50	800	150	800	120	T110H
TB1300H	120	5	160	3.5	50	800	150	800	120	T130H
TB1500H	140	5	180	3.5	50	800	150	800	120	T150H
TB1800H	160	5	220	3.5	50	800	150	800	120	T180H
TB2300H	190	5	265	3.5	50	800	150	800	80	T230H
TB2600H	220	5	300	3.5	50	800	150	800	80	T260H
TB3100H	275	5	350	3.5	50	800	150	800	80	T310H
TB3500H	320	5	400	3.5	50	800	150	800	80	T350H

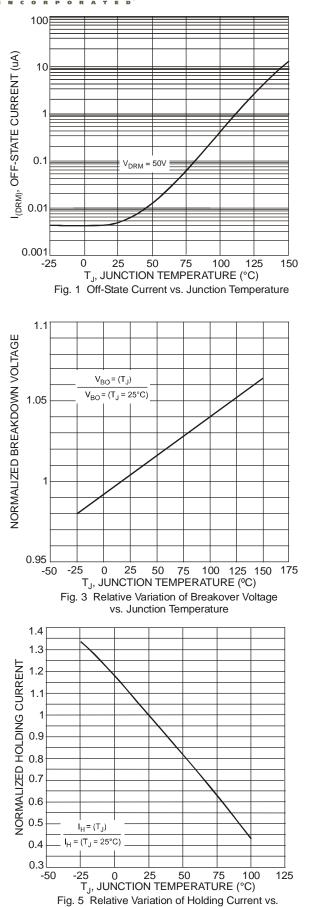
Symbol	Parameter	
V _{DRM}	Stand-off Voltage	
I _{DRM}	Leakage current at stand-off voltage	
V _{BR}	Breakdown voltage	
I _{BR}	Breakdown current	
V _{BO}	Breakover voltage	
I _{BO}	Breakover current	
Ін	Holding current (Note 5)	
VT	On state voltage	
IPP	Peak pulse current	
Co	Off-state capacitance (Note 6)	

Notes: 5. I_H > (V_L/R_L) If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time does not exceed 30ms.

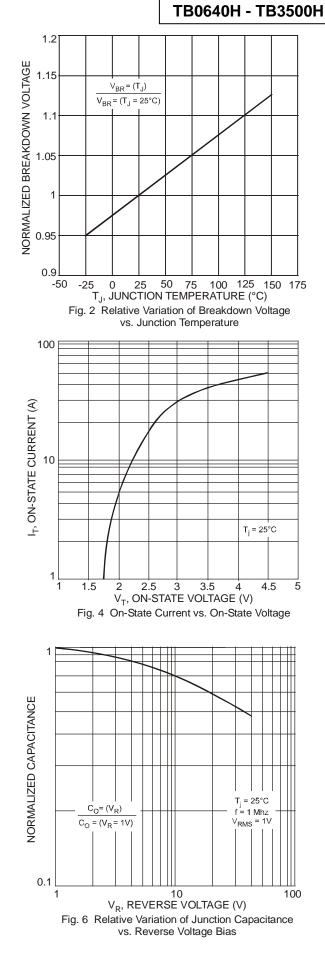
6. Off-state capacitance measured at f = 1.0MHz, 1.0V_{RMS} signal, V_R = 2V_{DC} bias.





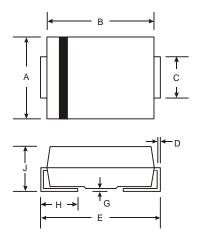


Junction Temperature



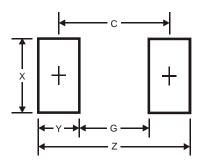


Package Outline Dimensions



SMB			
Dim	Dim Min Ma		
Α	3.30	3.94	
В	4.06	4.57	
С	1.96	2.21	
D	0.15	0.31	
ш	5.00	5.59	
G 0.05 0.20			
H	0.76	1.52	
J 2.00 2.50			
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	6.8
G	1.8
Х	2.3
Y	2.5
С	4.3



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